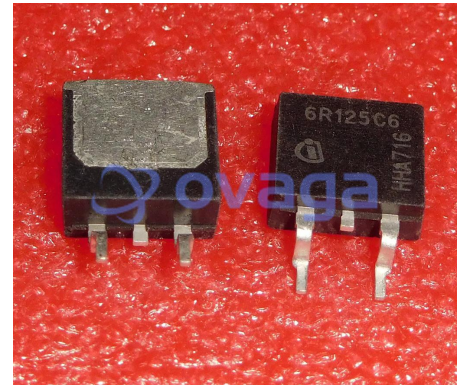


N-Channel MOSFETs (>500V...900V); Package: PG-TO263-3; VDS (max): 600.0 V;  
 Package: D2PAK (TO-263); RDS(ON) @ TJ=25°C VGS=10: 125.0 mOhm; ID(max) @  
 TC=25°C: 30.0 A; IDpuls (max): 89.0 A;

Manufacturers	<u>Infineon Technologies Corporation</u>
Package/Case	TO-263-3
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IPB60R125C6 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

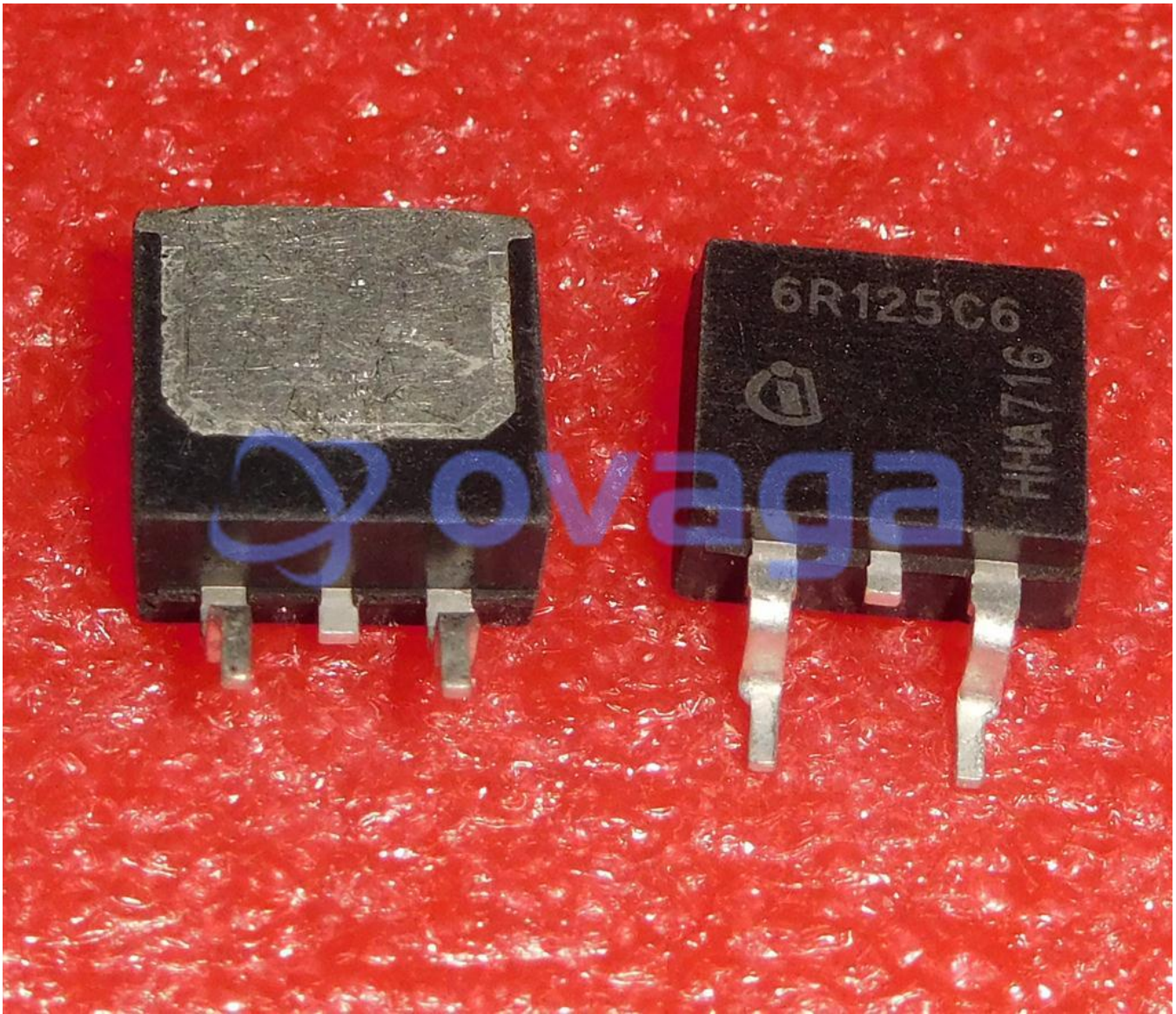
IPB60R125C6 is a power MOSFET (Metal-Oxide-Semiconductor Field-Effect Transistor) manufactured by Infineon Technologies.

### Features

- It has a voltage rating of 600V
- It can handle a continuous current of 26A
- It has a low on-resistance of 125mOhms
- It is designed for use in high-frequency switching applications
- It has a small form factor, making it suitable for use in space-constrained designs

### Application

- Switch-mode power supplies
- DC-DC converters
- Motor drives
- Inverters
- Lighting ballasts







## Related Products



### [IPP60R070CFD7](#)

Infineon Technologies Corporation  
TO-220-3



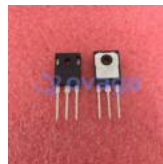
### [IPB180N06S4-H1](#)

Infineon Technologies Corporation  
PG-TO263-7-3



### [IPG20N04S4-12](#)

Infineon Technologies Corporation  
TDSON-8



### [IPW65R080CFD](#)

Infineon Technologies Corporation  
TO-247



[IPD25N06S4L-30](#)

Infineon Technologies Corporation  
PG-TO252-3



[IPD180N10N3G](#)

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TO-252



[IPP60R074C6](#)

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TO-220-3



[IPD70R1K4P7S](#)

Infineon Technologies Corporation  
TO252-3